ESDONCAN1, SESDONCAN1

CAN/CAN-FD Bus Protector

Low Capacitance ESD Protection Diode for CAN/CAN−FD Bus

The S/ESDONCAN1 has been designed to protect the CAN transceiver from ESD and other harmful transient voltage events. This device provides bidirectional protection for each data line with a single compact SOT−23 package, giving the system designer a low cost option for improving system reliability and meeting stringent EMI requirements.

Features

- 200 W Peak Power Dissipation per Line (8 x 20 μsec Waveform)
- Diode Capacitance Matching
- Low Reverse Leakage Current (< 100 nA)
- Low Capacitance High−Speed FlexRay Data Rates
- IEC Compatibility: − IEC 61000−4−2 (ESD): Level 4
  − IEC 61000−4−4 (EFT): 50 A – 5/50 ns
  − IEC 61000−4−5 (Lighting) 3.0 A (8/20 μs)
- ISO 7637−1, Nonrepetitive EMI Surge Pulse 2, 8.0 A (1 x 50 μs)
- ISO 7637−3, Repetitive Electrical Fast Transient (EFT) EMI Surge Pulses, 50 A (5 x 50 ns)
- Flammability Rating UL 94 V−0
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable
- These are Pb−Free Devices

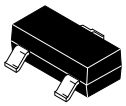
Typical Applications

- Industrial
  - Smart Distribution Systems (SDS)
  - DeviceNet
- Automotive
  - Controlled Area Network − CAN 2.1 / CAN FD
  - Low and High Speed CAN

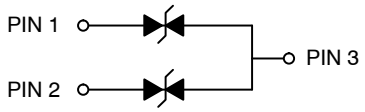
ON Semiconductor®

www.onsemi.com

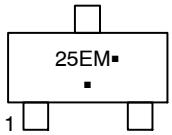
SOT−23
DUAL BIDIRECTIONAL
VOLTAGE SUPPRESSOR
200 W PEAK POWER



SOT−23
CASE 318
STYLE 27



MARKING DIAGRAM



25E = Device Code
M = Date Code
▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MAXIMUM RATINGS (T_J = 25°C, unless otherwise specified)

Symbol	Rating	Value	Unit
PPK	Peak Power Dissipation, 8 x 20 μs Double Exponential Waveform (Note 1)	200	W
T_J	Operating Junction Temperature Range	−55 to 150	°C
T_J	Storage Temperature Range	−55 to 150	°C
T_L	Lead Solder Temperature (10 s)	260	°C
ESD	Human Body Model (HBM) Machine Model (MM) IEC 61000−4−2 Specification (Contact)	8.0 400 23	kV V kV

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Non−repetitive current pulse per Figure 1.

ELECTRICAL CHARACTERISTICS (T_J = 25°C, unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
V_{RWM}	Reverse Working Voltage	(Note 2)	24	–	–	V
V_{BR}	Breakdown Voltage	I_T = 1 mA (Note 3)	26.2	–	32	V
I_R	Reverse Leakage Current	V_{RWM} = 24 V	–	15	100	nA
V_C	Clamping Voltage	I_{PP} = 1 A (8 x 20 μs Waveform) (Note 4)	–	33.4	36.6	V
V_C	Clamping Voltage	I_{PP} = 3 A (8 x 20 μs Waveform) (Note 4)	–	44	50	V
I_{PP}	Maximum Peak Pulse Current	8 x 20 μs Waveform (Note 4)	–	–	3.0	A
C_J	Capacitance	V_R = 0 V, f = 1 MHz (Line to GND)	–	–	10	pF
ΔC	Diode Capacitance Matching	V_R = 0 V, 5 MHz (Note 5)	–	0.26	2	%

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Surge protection devices are normally selected according to the working peak reverse voltage (V_{RWM}), which should be equal or greater than the DC or continuous peak operating voltage level.
3. V_{BR} is measured at pulse test current I_T.
4. Pulse waveform per Figure 1.
5. ΔC is the percentage difference between C_J of lines 1 and 2 measured according to the test conditions given in the electrical characteristics table.

ORDERING INFORMATION

Device	Package	Shipping†
ESDONCAN1LT1G	SOT−23 (Pb−Free)	3,000 / Tape & Reel
SESDONCAN1LT1G*	SOT−23 (Pb−Free)	3,000 / Tape & Reel
ESDONCAN1LT3G	SOT−23 (Pb−Free)	10,000 / Tape & Reel
SESDONCAN1LT3G*	SOT−23 (Pb−Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC−Q101 Qualified and PPAP Capable.

TYPICAL PERFORMANCE CURVES

(T_J = 25°C unless otherwise noted)

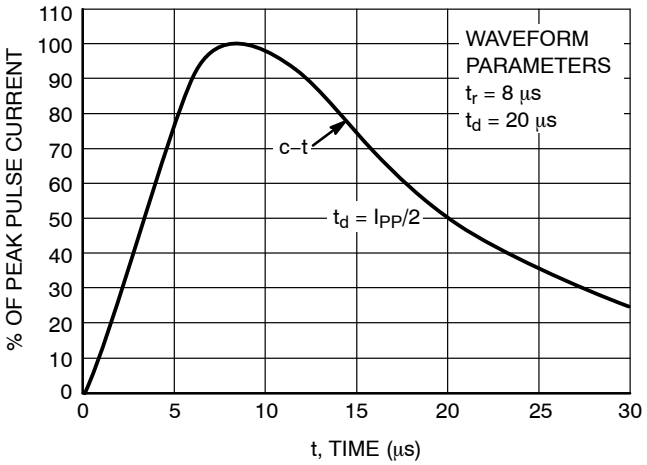


Figure 1. Pulse Waveform, 8 × 20 μs

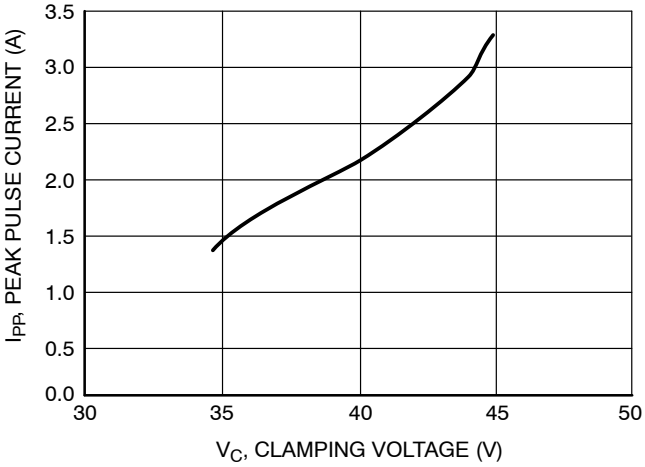


Figure 2. Clamping Voltage vs Peak Pulse Current

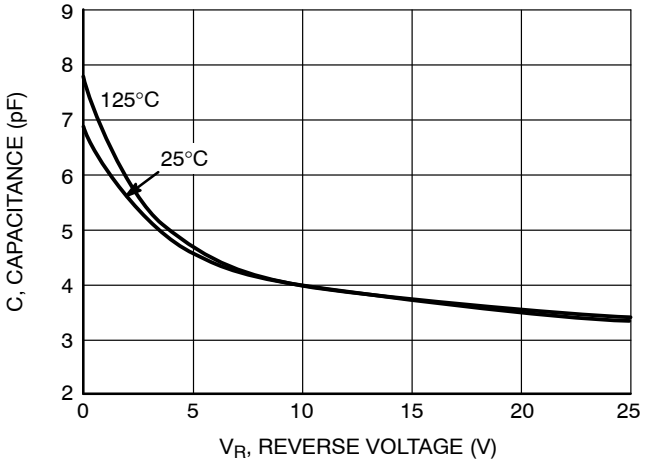


Figure 3. Typical Junction Capacitance vs Reverse Voltage

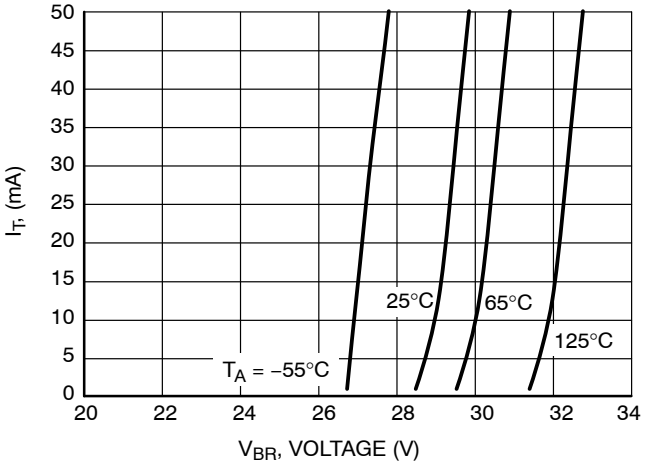


Figure 4. V_{BR} versus I_T Characteristics

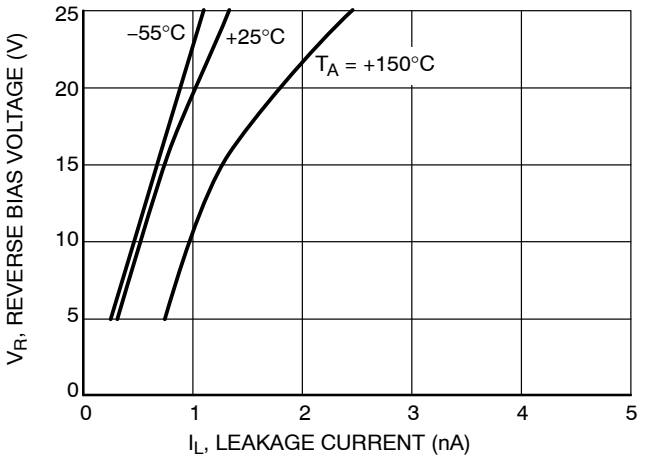


Figure 5. I_R versus Temperature Characteristics

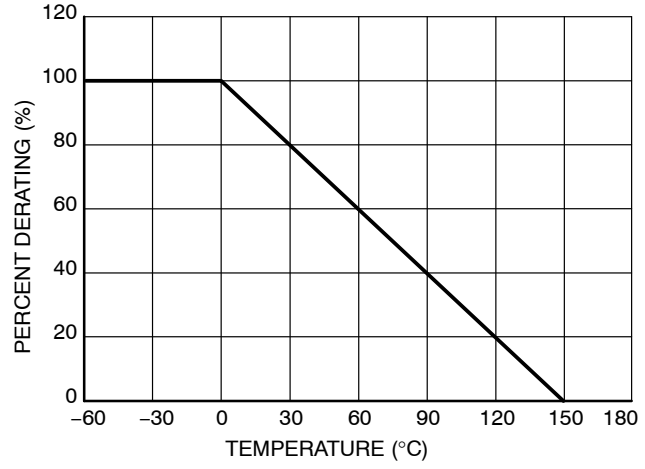


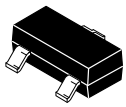
Figure 6. Temperature Power Dissipation Derating

APPLICATIONS

Background

The Controller Area Network (CAN) is a serial communication protocol designed for providing reliable high speed data transmission in harsh environments. Surge protection diodes provide a low cost solution to conducted and radiated Electromagnetic Interference (EMI) and Electrostatic Discharge (ESD) noise problems. The noise immunity level and reliability of CAN transceivers can be easily increased by adding external surge protection diodes to prevent transient voltage failures. The ESDONCAN1 provides a surge protection solution for CAN data communication lines. The ESDONCAN1 is a low capacitance dual bidirectional surge protection device in a compact SOT-23 package especially suitable for CAN2.1 (CAN-FD). This device is based on Zener technology that optimizes the active area of a PN junction to provide robust protection against transient EMI surge voltage and ESD. The ESDONCAN1 has been tested to EMI and ESD levels that exceed the specifications of popular high speed CAN networks.

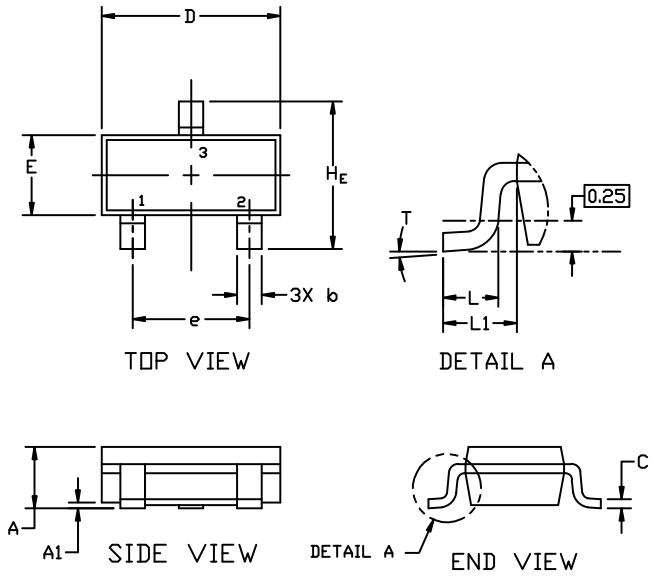
MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS



SCALE 4:1

SOT−23 (TO−236)
CASE 318
ISSUE AT

DATE 01 MAR 2023

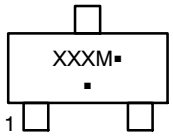


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

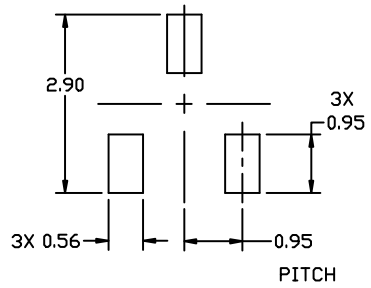
	MILLIMETERS			INCHES		
DIM	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
H_E	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLES ON PAGE 2

DOCUMENT NUMBER:	**98ASB42226B**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red.	
DESCRIPTION:	**SOT−23 (TO−236)**		**PAGE 1 OF 2**

SOT−23 (TO−236)
CASE 318
ISSUE AT

DATE 01 MAR 2023

STYLE 1 THRU 5:
CANCELLED

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE

STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE−ANODE

STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE

STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE

STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE

STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE

STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE−ANODE

STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT

STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE

STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION

STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE

STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales